# FDBL0630N150

# MOSFET – N-Channel, POWERTRENCH®

## 150 V, 169 A, 6.3 mΩ

### Features

- Typ $r_{DS(on)}$ = 5 mΩ at $V_{GS}$ = 10 V, $I_D$ = 80 A
- Typ $Q_{g(tot)}$ = 70 nC at $V_{GS}$ = 10 V, $I_D$ = 80 A
- UIS Capability
- This Device is Pb−Free and is RoHS Compliant

### Applications

- Industrial Motor Drive
- Industrial Power Supply
- Industrial Automation
- Battery Operated tools
- Battery Protection
- Solar Inverters
- UPS and Energy Inverters
- Energy Storage
- Load Switch

**MAXIMUM RATINGS** ($T_J$ = 25°C, unless otherwise specified)

| Symbol | Parameter | Ratings | Unit |
|---|---|---|---|
| VDSS | Drain to Source Voltage | 150 | V |
| VGS | Gate to Source Voltage | ±20 | V |
| $I_D$ | Drain Current – Continuous ($V_{GS}$ = 10 V) (Note 1) $T_C$ = 25°C | 169 | A |
| | Pulsed Drain Current $T_C$ = 25°C | See Figure 4 | |
| EAS | Single Pulse Avalanche Energy (Note 2) | 502 | mJ |
| $P_D$ | Power Dissipation | 500 | W |
| | Derate above 25°C | 3.3 | W/°C |
| $T_J$, $T_{STG}$ | Operating and Storage Temperature | −55 to +175 | °C |
| $R_{\theta JC}$ | Thermal Resistance Junction to Case | 0.3 | °C/W |
| $R_{\theta JA}$ | Maximum Thermal Resistance Junction to Ambient (Note 3) | 43 | °C/W |

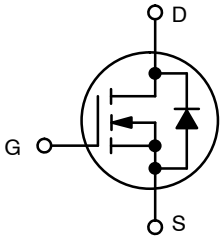
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Current is limited by junction temperature.
2. Starting $T_J$ = 25°C, L = 0.24 mH, $I_{AS}$ = 64 A, $V_{DD}$ = 100 V during inductor charging and $V_{DD}$ = 0 V during time in avalanche.
3. $R_{\theta JA}$ is the sum of the junction−to−case and case−to−ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design. The maximum rating presented here is based on mounting on a 1 $in^2$ pad of 2 oz copper.

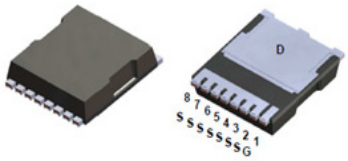
**ON Semiconductor®**

www.onsemi.com

| $V_{DSS}$ | $r_{DS(ON)}$ MAX | $I_D$ MAX |
|---|---|---|
| 150 V | 6.3 mΩ @ 10 V | 169 A |




**MOSFET — N−Channel**




**H−PSOF8L 11.68x9.80**
**CASE 100CU**

### MARKING DIAGRAM


$Y = ON Semiconductor Logo
&Z = Assembly Plant Code
&3 = Date Code
&K = Lot Run Traceability Code
FDBL0630N150 = Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

**ELECTRICAL CHARACTERISTICS** ($T_J$ = 25°C unless otherwise noted)

| Symbol | Parameter | Test Condition | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | | |
| $B_{VDSS}$ | Drain to Source Breakdown Voltage | $I_D$ = 250 μA, $V_{GS}$ = 0 V | | 150 | – | – | V |
| $I_{DSS}$ | Drain to Source Leakage Current | $V_{DS}$ = 150 V, $V_{GS}$ = 0 V | $T_J$ = 25°C | – | – | 1 | μA |
| | | | $T_J$ = 175°C (Note 4) | – | – | 1 | mA |
| $I_{GSS}$ | Gate to Source Leakage Current | $V_{GS}$ = ±20 V | | – | – | ±100 | nA |
| **ON CHARACTERISTICS** | | | | | | | |
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS}$ = $V_{DS}$, $I_D$ = 250 μA | | 2.0 | 2.8 | 4.0 | V |
| $r_{DS(on)}$ | Drain to Source On Resistance | $I_D$ = 80 A, $V_{GS}$ = 10 V | $T_J$ = 25°C | – | 5 | 6.3 | mΩ |
| | | | $T_J$ = 175°C (Note 4) | – | 14 | 17.5 | mΩ |
| **DYNAMIC CHARACTERISTICS** | | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = 75V, $V_{GS}$ = 0V, f = 1 MHz | | – | 5805 | – | pF |
| $C_{oss}$ | Output Capacitance | | | – | 536 | – | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | | – | 16 | – | pF |
| $R_g$ | Gate Resistance | f = 1 MHz | | – | 2.2 | – | Ω |
| $Q_{g(ToT)}$ | Total Gate Charge at 10 V | $V_{GS}$ = 0 to 10 V, $V_{DD}$ = 75 V, $I_D$ = 80 A | | – | 70 | 90 | nC |
| $Q_{g(th)}$ | Threshold Gate Charge | $V_{GS}$ = 0 to 2 V, $V_{DD}$ = 75 V, $I_D$ = 80 A | | – | 10.5 | 13 | nC |
| $Q_{gs}$ | Gate to Source Gate Charge | $V_{DD}$ = 75 V, $I_D$ = 80 A | | – | 32.5 | – | nC |
| $Q_{gd}$ | Gate to Drain “Miller” Charge | $V_{DD}$ = 75 V, $I_D$ = 80 A | | – | 10 | – | nC |
| **SWITCHING CHARACTERISTICS** | | | | | | | |
| $t_{on}$ | Turn−On Time | $V_{DD}$ = 75 V, $I_D$ = 80 A, $V_{GS}$ = 10 V, $R_{GEN}$ = 6 Ω | | – | – | 80 | ns |
| $t_{d(on)}$ | Turn−On Delay Time | | | – | 39 | – | ns |
| $t_r$ | Rise Time | | | – | 30 | – | ns |
| $t_{d(off)}$ | Turn−Off Delay Time | | | – | 70 | – | ns |
| $t_f$ | Fall Time | | | – | 23 | – | ns |
| $t_{off}$ | Turn−Off Time | | | – | – | 130 | ns |
| **DRAIN−SOURCE DIODE CHARACTERISTICS** | | | | | | | |
| $V_{SD}$ | Source to Drain Diode Voltage | $I_{SD}$ = 80 A, $V_{GS}$ = 0 V | | – | – | 1.25 | V |
| | | $I_{SD}$ = 40 A, $V_{GS}$ = 0 V | | – | – | 1.2 | V |
| $T_{rr}$ | Reverse Recovery Time | $I_F$ = 80 A, $dI_{SD}/dt$ = 100 A/μs, $V_{DD}$ = 120 V | | – | 108 | 125 | ns |
| $Q_{rr}$ | Reverse Recovery Charge | | | – | 323 | 467 | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The maximum value is specified by design at $T_J$ = 175°C. Product is not tested to this condition in production.

## TYPICAL CHARACTERISTICS

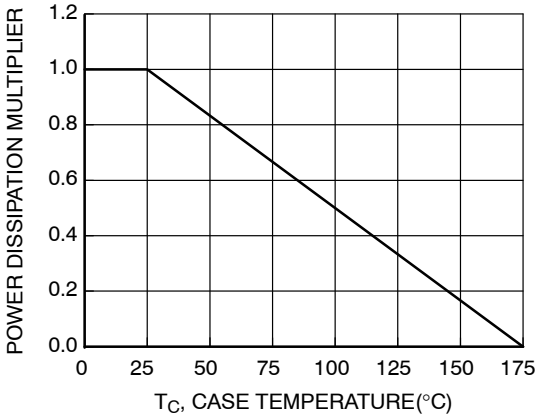



**Figure 1. Normalized Power Dissipation vs. Case Temperature**

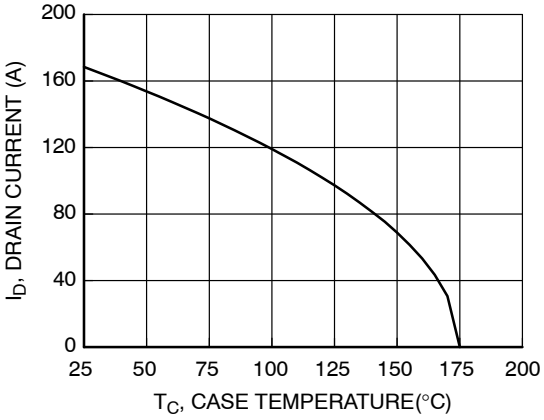



**Figure 2. Maximum Continuous Drain Current vs. Case Temperature**

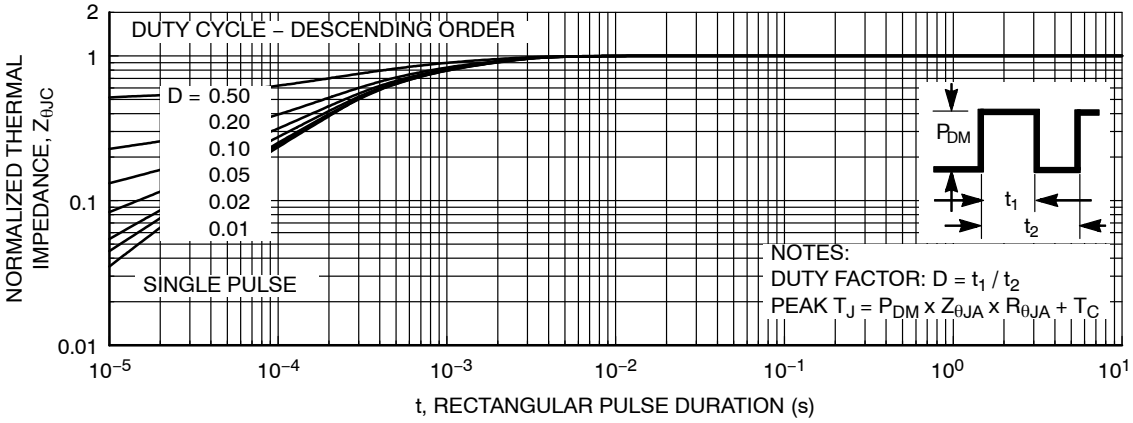



**Figure 3. Normalized Maximum Transient Thermal Impedance**

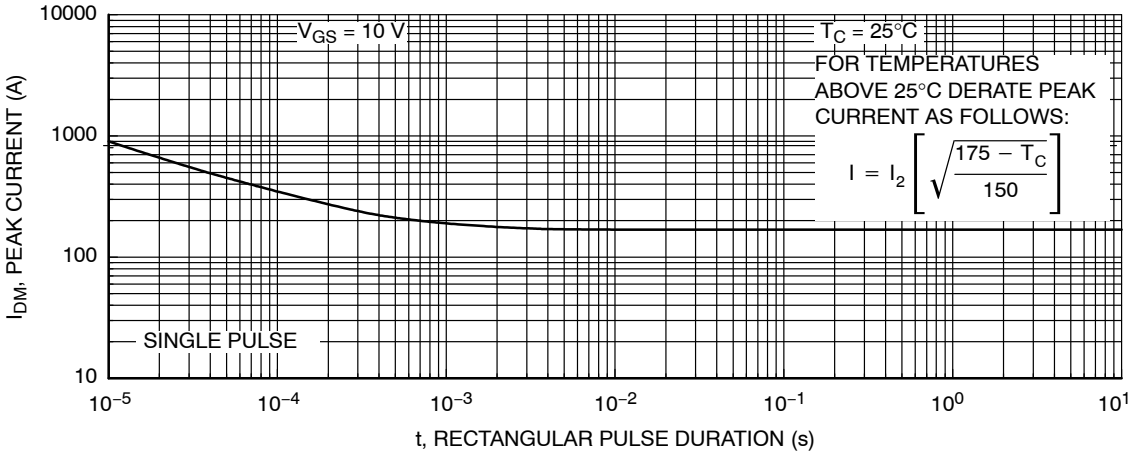



**Figure 4. Peak Current Capability**

## TYPICAL CHARACTERISTICS (continued)

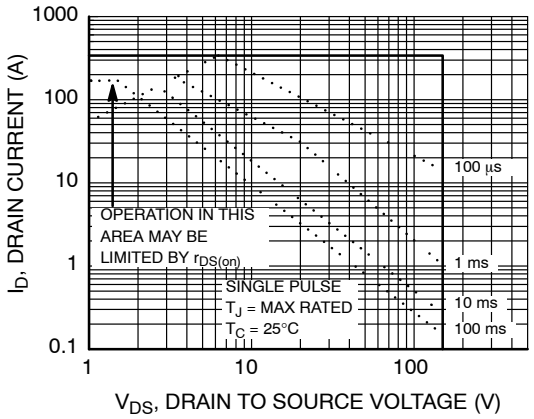
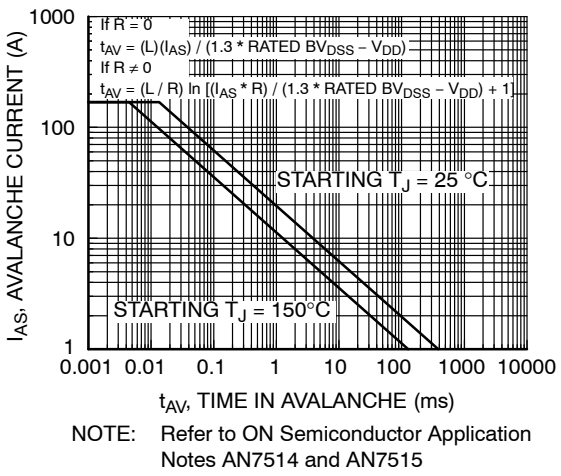



**Figure 5. Forward Bias Safe Operating Area**




NOTE: Refer to ON Semiconductor Application Notes AN7514 and AN7515

**Figure 6. Unclamped Inductive Switching Capability**

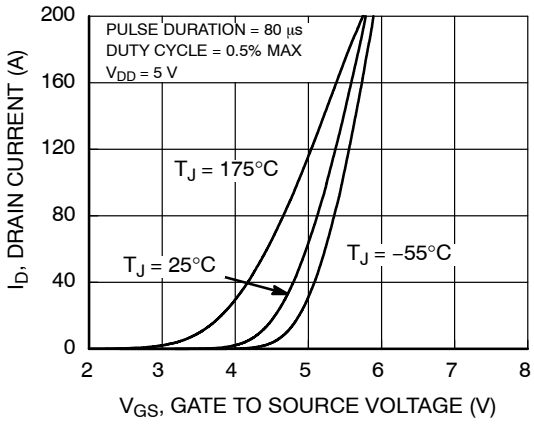



**Figure 7. Transfer Characteristics**

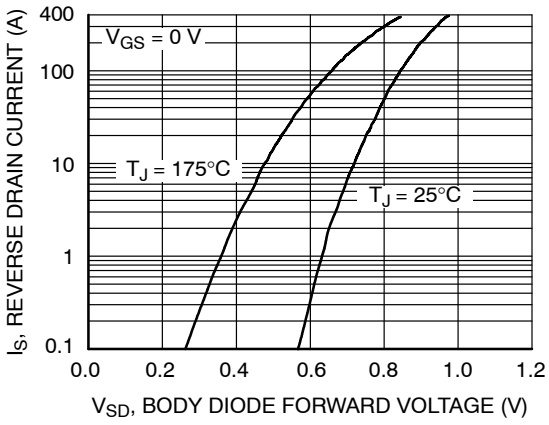



**Figure 8. Forward Diode Characteristics**

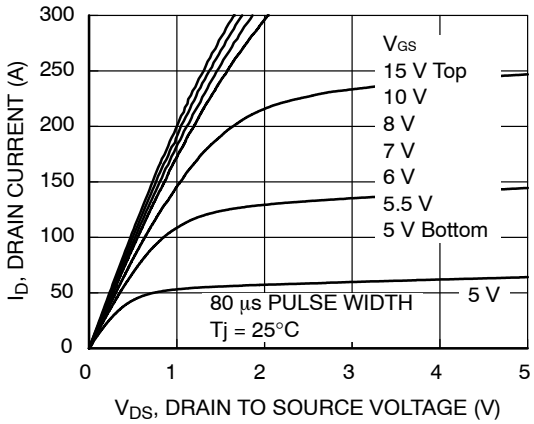



**Figure 9. Saturation Characteristics**

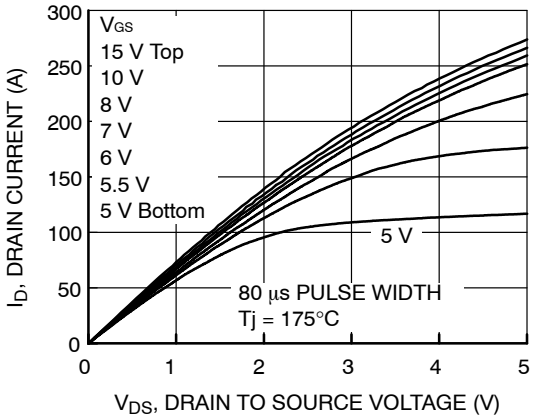



**Figure 10. Saturation Characteristics**

## TYPICAL CHARACTERISTICS (continued)

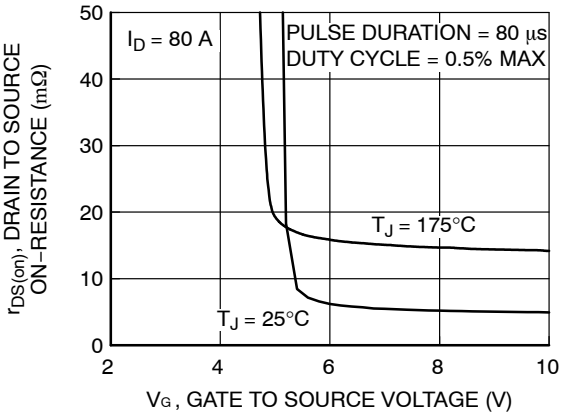



**Figure 11. Rdson vs. Gate Voltage**

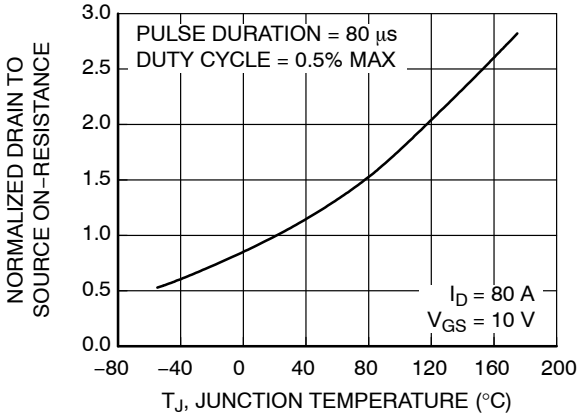



**Figure 12. Normalized Rdson vs. Junction Temperature**

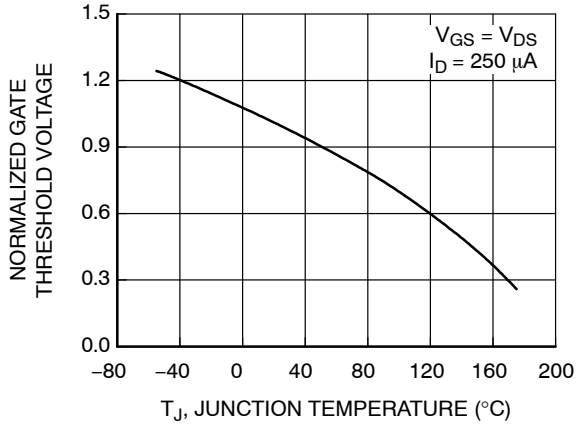



**Figure 13. Normalized Gate Threshold Voltage vs. Temperature**

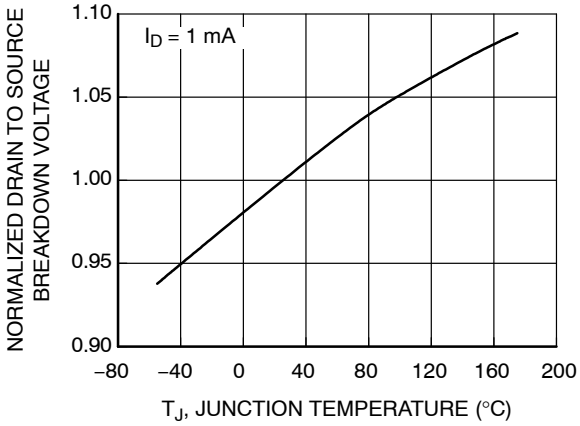



**Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature**

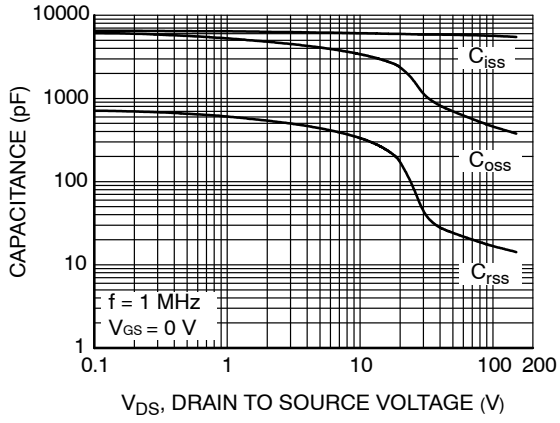



**Figure 15. Capacitance vs Drain to Source Voltage**

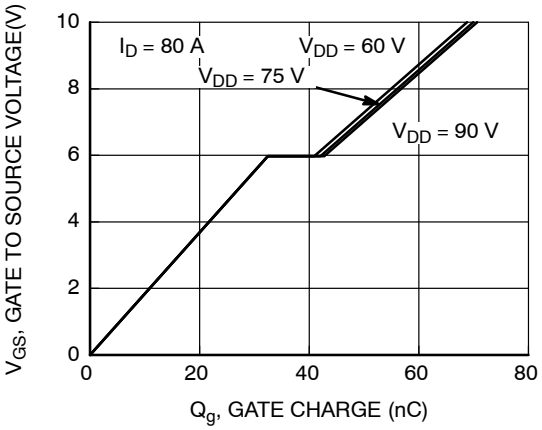
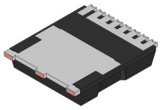



**Figure 16. Gate Charge vs Gate to Source Voltage**

## ORDERING INFORMATION

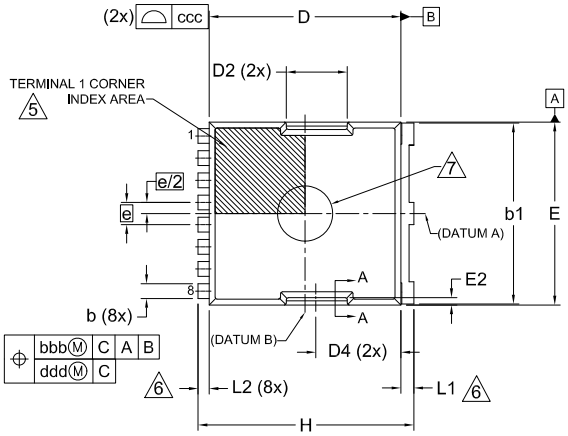
| Device | Device Marking | Package | Shipping† |
|---|---|---|---|
| FDBL0630N150 | FDBL0630N150 | H−PSOF8L 11.68x9.80<br>(Pb−Free) | 2000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

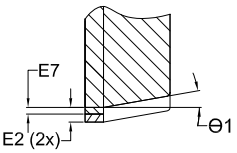


## H−PSOF8L 11.68x9.80x2.30, 1.20P
CASE 100CU
ISSUE F

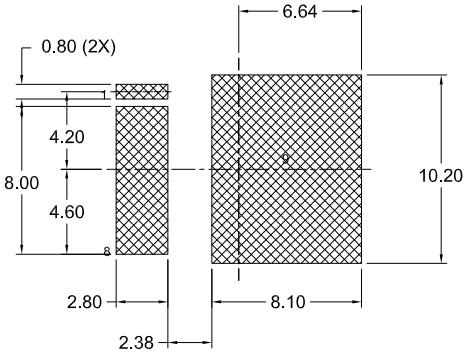
DATE 30 JUL 2024




TOP VIEW

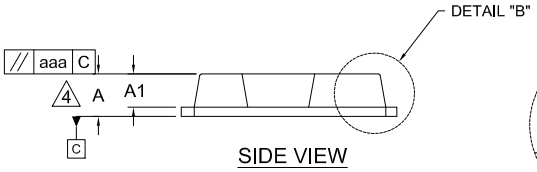



SECTION "A-A"
SCALE: 2X

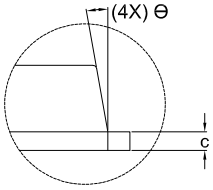



LAND PATTERN RECOMMENDATION

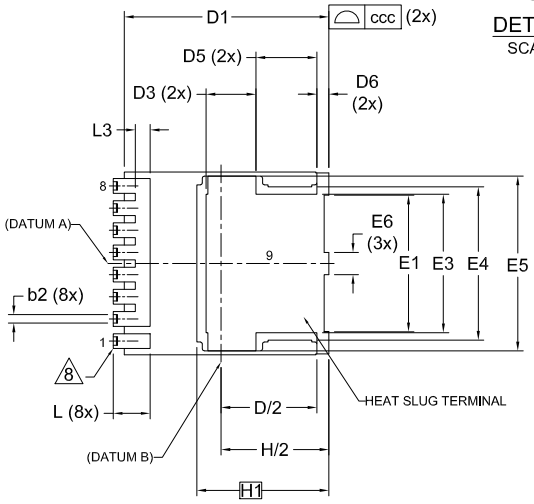
*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.




SIDE VIEW




DETAIL "B"
SCALE: 2X



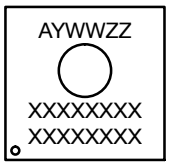

BOTTOM VIEW

NOTES:
1. PACKAGE STANDARD REFERENCE: JEDEC MO-299, ISSUE B.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
3. "e" REPRESENTS THE TERMINAL PITCH.
4. THIS DIMENSION INCLUDES ENCAPSULATION THICKNESS "A1", AND PACKAGE BODY THICKNESS, BUT DOES NOT INCLUDE ATTACHED FEATURES, e.g.,EXTERNAL OR CHIP CAPACITORS. AN INTEGRAL HEATSLUG IS NOT CONSIDERED AS ATTACHED FEATURE.
5. A VISUAL INDEX FEATURE MUST BE LOCATED WITHIN THE HATCHED AREA.
6. DIMENSIONS b1,L1,L2 APPLY TO PLATED TERMINALS.
7. THE LOCATION AND SIZE OF EJECTOR MARKS ARE OPTIONAL.
8. THE LOCATION AND NUMBER OF FUSED LEADS ARE OPTIONAL.

| DIM | MILLIMETERS | | |
|---|---|---|---|
| | MIN. | NOM. | MAX. |
| A | 2.20 | 2.30 | 2.40 |
| A1 | 1.70 | 1.80 | 1.90 |
| b | 0.70 | 0.80 | 0.90 |
| b1 | 9.70 | 9.80 | 9.90 |
| b2 | 0.35 | 0.45 | 0.55 |
| c | 0.40 | 0.50 | 0.60 |
| D | 10.28 | 10.38 | 10.48 |
| D/2 | 5.09 | 5.19 | 5.29 |
| D1 | 10.98 | 11.08 | 11.18 |
| D2 | 3.20 | 3.30 | 3.40 |
| D3 | 2.60 | 2.70 | 2.80 |
| D4 | 4.45 | 4.55 | 4.65 |
| D5 | 3.20 | 3.30 | 3.40 |
| D6 | 0.55 | 0.65 | 0.75 |
| E | 9.80 | 9.90 | 10.00 |
| E1 | 7.30 | 7.40 | 7.50 |
| E2 | 0.30 | 0.40 | 0.50 |
| E3 | 7.40 | 7.50 | 7.60 |
| E4 | 8.20 | 8.30 | 8.40 |

| DIM | MILLIMETERS | | |
|---|---|---|---|
| | MIN. | NOM. | MAX. |
| E5 | 9.36 | 9.46 | 9.56 |
| E6 | 1.10 | 1.20 | 1.30 |
| E7 | 0.15 | 0.18 | 0.21 |
| e | 1.20 BSC | | |
| e/2 | 0.60 BSC | | |
| H | 11.58 | 11.68 | 11.78 |
| H/2 | 5.74 | 5.84 | 5.94 |
| H1 | 7.15 BSC | | |
| L | 1.90 | 2.00 | 2.10 |
| L1 | 0.60 | 0.70 | 0.80 |
| L2 | 0.50 | 0.60 | 0.70 |
| L3 | 0.70 | 0.80 | 0.90 |
| Θ | 10° REF | | |
| Θ1 | 10° REF | | |
| aaa | 0.20 | | |
| bbb | 0.25 | | |
| ccc | 0.20 | | |
| ddd | 0.20 | | |
| eee | 0.10 | | |

### GENERIC MARKING DIAGRAM*




A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code
XXXX = Specific Device Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

| | | |
|---|---|---|
| **DOCUMENT NUMBER:** | **98AON13813G** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red. |
| **DESCRIPTION:** | **H−PSOF8L 11.68x9.80x2.30, 1.20P** | **PAGE 1 OF 1** |

## ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS**:
**Technical Library:** www.onsemi.com/design/resources/technical−documentation
**onsemi Website:** www.onsemi.com

**ONLINE SUPPORT**: www.onsemi.com/support
**For additional information, please contact your local Sales Representative at** www.onsemi.com/support/sales